PROCESS CPD04

General Purpose Rectifier

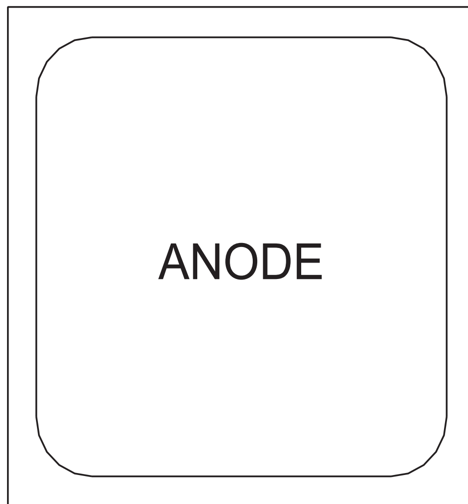
500mA Glass Passivated Rectifier Chip

Central™ Semiconductor Corp.

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	25 x 25 MILS
Die Thickness	9.5 MILS
Anode Bonding Pad Area	14.5 x 14.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



R0

GROSS DIE PER 4 INCH WAFER
18,080

PRINCIPAL DEVICE TYPES
1N645 thru 1N649
CBRHD-02 Series

The Typical Electrical Characteristics data for this chip is currently being revised.

For the latest updated data for this Chip Process, please visit our website at:

www.centralsemi.com/chip

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R1 (1-August 2002)